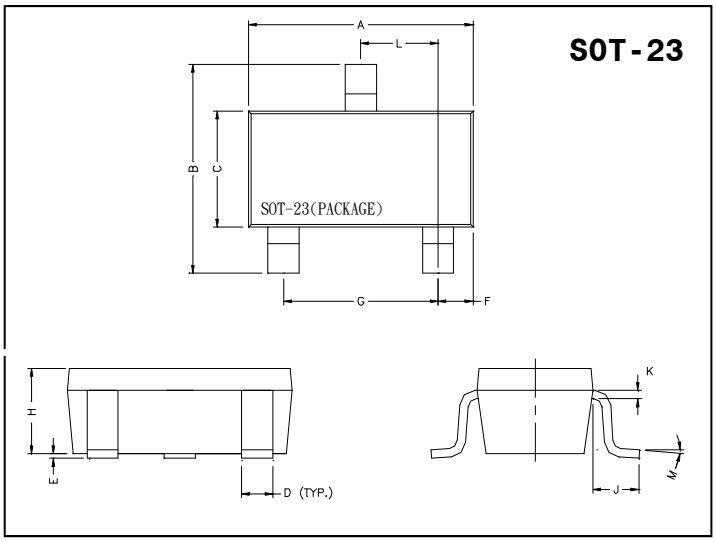
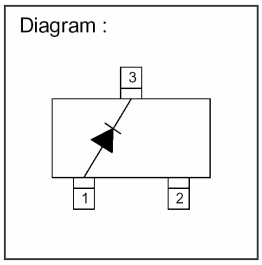
GMBD4148

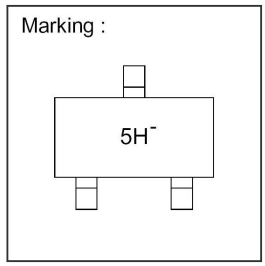
Description

The GMBD4148 is designed for high-speed switching application in hybrid thick-and thin-film circuits. The devices is manufactured by the silicon epitaxial planar process and packed in plastic surface mount package.

Package Dimensions







Style : Pin 1.Anode 2.NC 3.Cathode

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-65~+150	℃
Continuous Reverse Voltage	V_R	70	V
Continuous Forward Current	I_F	200	mA
Peak Forward Surge Current	I_{FSM}	500	mA

Characteristics at Ta = 25℃

Characteristic	Symbol	Min.	Max.	Unit	Test Conditions
Forward Voltage	VF	-	1	V	IF=10mA
Reverse Breakdown	VR	100	-	V	IR=100uA
Reverse Current	IR	-	5	uA	VR=75V
Total Capacitance	CT	-	4	pF	VR=0V,F=1MHz
Reverse Recovery Time	Trr	-	4	nS	IF=IR=10mA, RL=100Ω Measured at IR=1mA

Head Office And Factory:
- **Taiwan**: No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
  TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China**: (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
  TEL : 86-21-5895-7671 FAX : 86-21-38950165